



4N65-S

Power MOSFET

4A, 650V N-CHANNEL POWER MOSFET

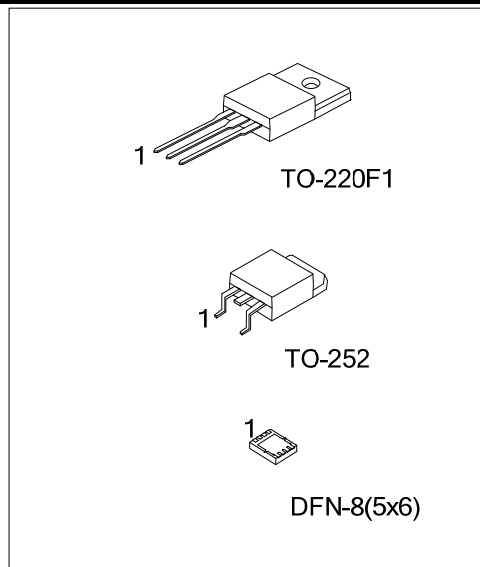
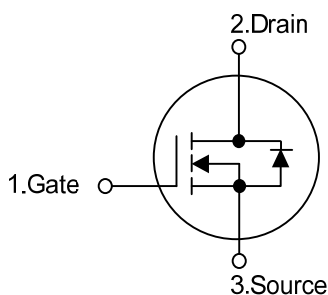
DESCRIPTION

The UTC **4N65-S** is a high voltage power MOSFET designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristic. This power MOSFET is usually used in high speed switching applications including power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

FEATURES

- * $R_{DS(ON)} < 2.9\Omega @ V_{GS} = 10V, I_D = 2A$
- * Fast Switching Capability
- * Avalanche Energy Specified
- * Improved dv/dt Capability, High Ruggedness

SYMBOL



ORDERING INFORMATION

Ordering Number		Package	Pin Assignment								Packing
Lead Free	Halogen Free		1	2	3	4	5	6	7	8	
4N65L-TF1-T	4N65G-TF1-T	TO-220F1	G	D	S	-	-	-	-	-	Tube
4N65L-TN3-T	4N65G-TN3-T	TO-252	G	D	S	-	-	-	-	-	Tape Reel
-	4N65G-K08-5060-R	DFN-8(5x6)	S	S	S	G	D	D	D	D	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>4N65L-TF1-T</p> <p>(1)Packing Type (2)Package Type (3)Green Package</p>	<p>(1) T: Tube, R: Tape Reel (2) TF1: TO-220F1, TN3: TO-252, K08-5060: DFN-8(5x6) (3) L: Lead Free, G: Halogen Free and Lead Free</p>
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MARKING

TO-220F1 / TO-252	DFN-8(5x6)

■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous	I_D	4.0	A
	Pulsed (Note2)	I_{DM}	16	A
Avalanche Energy	Single Pulsed (Note3)	E_{AS}	150	mJ
Peak Diode Recovery dv/dt (Note4)		dv/dt	4.5	V/ns
Power Dissipation	TO-220F1	P_D	36	W
	TO-252		50	W
	DFN-8(5×6)		30	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Operating Temperature		T_{OPR}	-55 ~ +150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L = 18.75\text{mH}$, $I_{AS} = 4\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 4\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER	PACKAGE	SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220F1	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
	TO-252		110	$^\circ\text{C}/\text{W}$
	DFN-8(5×6)		75 (Note)	$^\circ\text{C}/\text{W}$
Junction to Case	TO-220F1	θ_{JC}	3.47	$^\circ\text{C}/\text{W}$
	TO-252		2.5	$^\circ\text{C}/\text{W}$
	DFN-8(5×6)		4.17 (Note)	$^\circ\text{C}/\text{W}$

Note: Note: The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

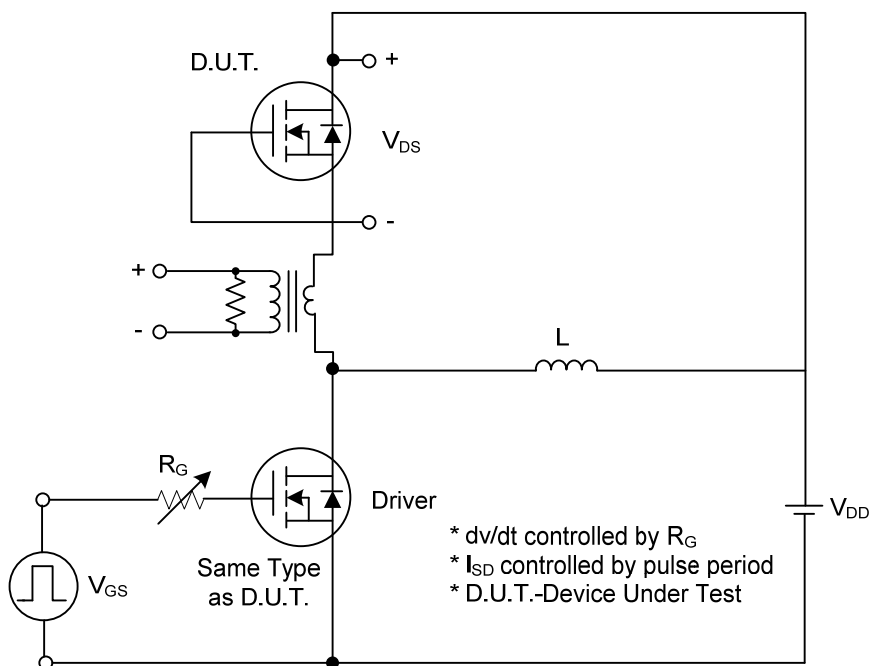
■ ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0 V, I _D = 250μA	650			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} = 650 V, V _{GS} = 0 V			10	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = 30 V, V _{DS} = 0 V			100	nA
		V _{GS} = -30 V, V _{DS} = 0 V			-100	nA
Breakdown Voltage Temperature Coefficient	ΔBV _{DSS} /ΔT _J	I _D =250μA, Referenced to 25°C		0.6		V/°C
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} = V _{GS} , I _D = 250μA	2.0		4.0	V
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 2A			2.9	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{ISS}	V _{DS} = 25 V, V _{GS} = 0V, f = 1MHz		420	550	pF
Output Capacitance	C _{OSS}			40	60	pF
Reverse Transfer Capacitance	C _{RSS}			4	8	pF
SWITCHING CHARACTERISTICS¹⁰						
Turn-On Delay Time	t _{D(ON)}	V _{DS} = 30 V, I _D = 0.5 A, R _G = 25Ω (Note 1, 2)		60		ns
Turn-On Rise Time	t _R			25		ns
Turn-Off Delay Time	t _{D(OFF)}			125		ns
Turn-Off Fall Time	t _F			30		ns
Total Gate Charge	Q _G	V _{DS} = 50 V, I _D = 1.3 A, V _{GS} = 10V (Note 1, 2)		15	20	nC
Gate-Source Charge	Q _{GS}			5		nC
Gate-Drain Charge	Q _{GD}			2		nC
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} = 0 V, I _S = 4A			1.4	V
Maximum Continuous Drain-Source Diode Forward Current	I _S				4	A
Maximum Pulsed Drain-Source Diode Forward Current	I _{SM}				16	A

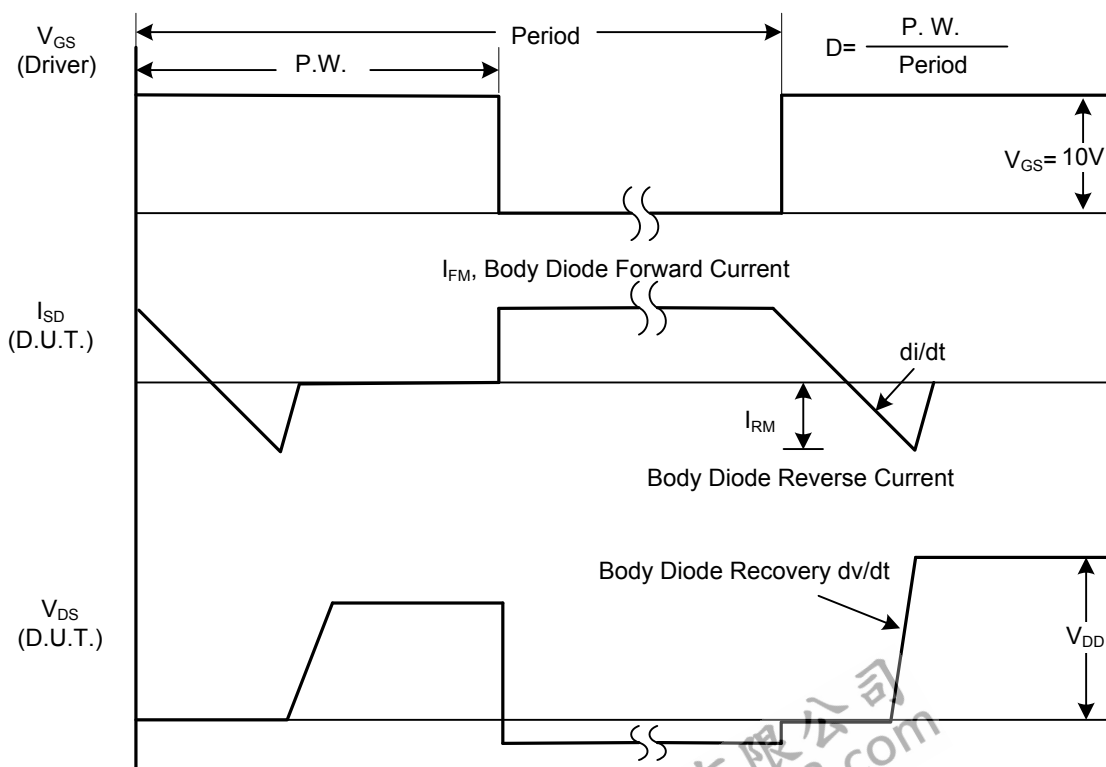
Note: 1. Pulse Test: Pulse width≤300μs, Duty cycle≤2%.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

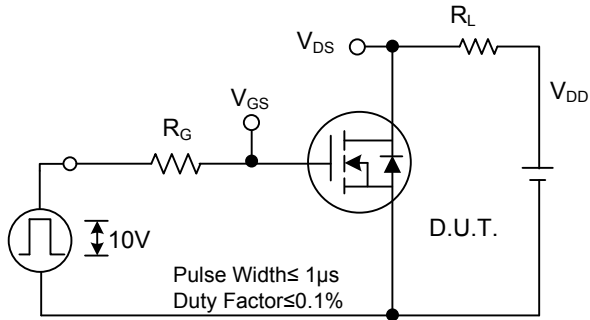


Peak Diode Recovery dv/dt Test Circuit

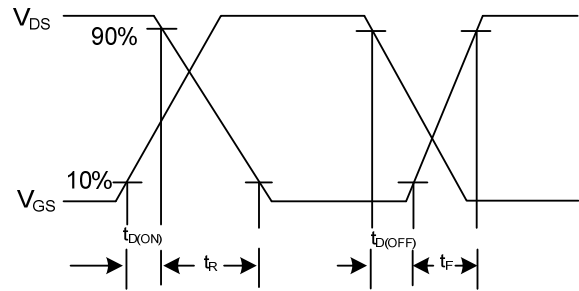


Peak Diode Recovery dv/dt Waveforms

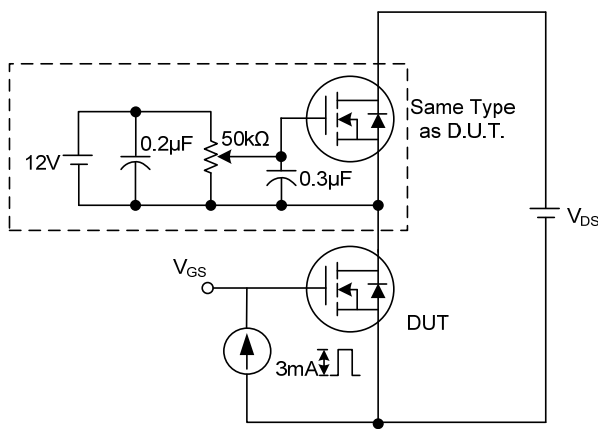
TEST CIRCUITS AND WAVEFORMS (Cont.)



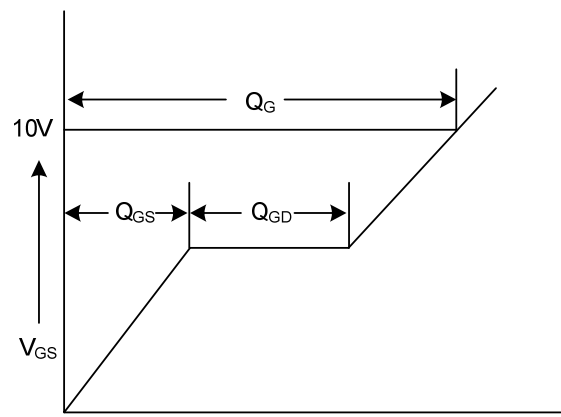
Switching Test Circuit



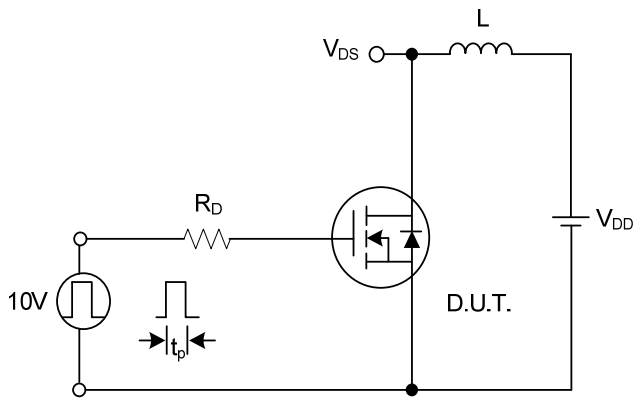
Switching Waveforms



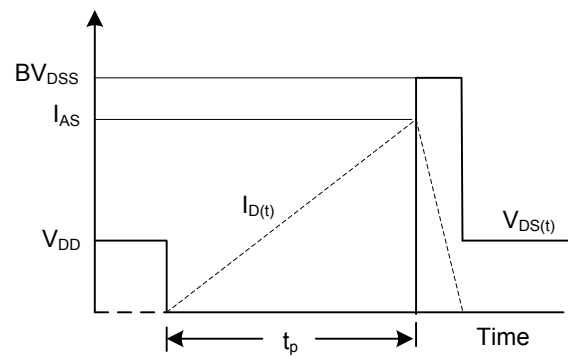
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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